

# SGM40642 5V eFuse with Precision Adjustable Current Limit and Over-Voltage Clamp

## **GENERAL DESCRIPTION**

The SGM40642 is a smart low voltage load switch with a full suite of protective features that can protect the source, device, and the load against a variety of fault conditions. This eFuse device is suitable for 2.5V to 5V loads and provides accurate and adjustable current limiting (170mA to 2.9A) and over-voltage clamping (5.45V). It can deliver 2.5A continues current to the load and its input tolerates up to 20V over-voltage. In over-voltage conditions, the internal switch is turned off to keep the load disconnected.

If the source voltage is high but still near 5V, the output will be clamped to 5.45V to protect the load. If the  $V_{\rm IN}$  voltage exceeds 7.6V, the load will be disconnected to prevent damage.

The SGM40642 has an internal  $55m\Omega$  power switch with current limit capability. This limit is programmable with a single external resistor (R<sub>ILIM</sub>). A persistent overload condition usually results in thermal shutdown and may cause cyclic ON and OFF periods to protect the device.

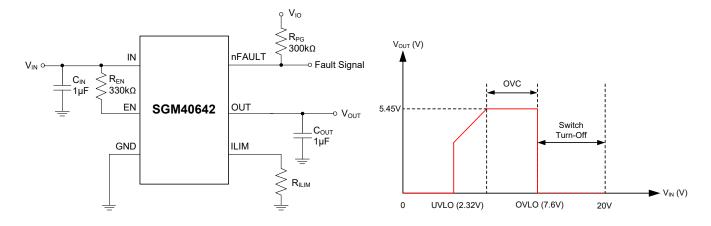
The SGM40642 is available in a Green TDFN-2×2-6AL package and can operate over the -40°C to +125°C ambient temperature range.

# FEATURES

- 2.5V to 6.5V Operation
- 55mΩ Internal Switch (High-side MOSFET)
- Up to 2.5A Continuous Load Current
- Up to 20V Input Over-Voltage Tolerance
- Output Shutoff at 7.6V Input Over-Voltage
- 100ns Over-Voltage Lockout (OVLO) Response
- 3.5µs Short Circuit Response
- Reverse Current Blocking while Disabled
- Built-In Soft-Start
- Pin-to-Pin Compatible with SGM2553
- -40°C to +125°C Operating Temperature Range
- Available in a Green TDFN-2×2-6AL Package

# **APPLICATIONS**

USB Power Switches USB Slave Devices Smart Phones/Cell Phones 3G, 4G Wireless Data-Cards Solid State Drives (SSD) 3V or 5V Adapter Powered Devices



# SIMPLIFIED SCHEMATIC

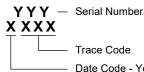


## PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM40642	TDFN-2×2-6AL	-40°C to +125°C	SGM40642XTDI6G/TR	R87 XXXX	Tape and Reel, 3000

### MARKING INFORMATION

NOTE: XXXX = Date Code and Trace Code.



- Date Code - Year

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

### **ABSOLUTE MAXIMUM RATINGS**

Voltage on IN (Referenced to GND) ..... -0.3V to 20V Voltage on OUT, EN (Referenced to GND)

-0.3V to 7V
Voltage on ILIM, nFAULT (Referenced to GND)
-0.3V to 6V
Voltage from IN to OUT (Referenced to GND)
-7V to 20V
Continuous Output Current, Io Thermally Limited
Continuous nFAULT Output Sink Current25mA (MAX)
Continuous ILIM Output Source Current150µA (MAX)
Package Thermal Resistance
TDFN-2×2-6AL, $\theta_{JA}$
Junction Temperature, T <sub>J</sub> +150°C
Storage Temperature Range65°C to +150°C
Lead Temperature (Soldering, 10s)+260°C

## **RECOMMENDED OPERATING CONDITIONS**

Input Voltage of IN, V <sub>IN</sub>	2.5V to 6.5V
Enable Terminal Voltage, V <sub>EN</sub>	0V to 6.5V
Continuous nFAULT Sink Current, InFAULT	0mA to 10mA
Continuous Output Current of OUT, IOUT	2.5A (MAX)
Current-Limit Set Resistor, RILIM	$33k\Omega$ to $1100k\Omega$
Operating Temperature Range	-40°C to +125°C

### **OVERSTRESS CAUTION**

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

### ESD SENSITIVITY CAUTION

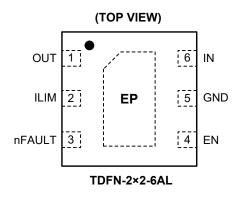
This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

### DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.



# **PIN CONFIGURATION**



# **PIN DESCRIPTION**

PIN	NAME	I/O	FUNCTION
1	OUT	0	Power Switch Output Pin. Connect this pin to the load.
2	ILIM	0	Current Limit Programming Pin. Connect a resistor ( $R_{ILIM}$ ) between this pin and the GND to set the current limit threshold. Recommended range for this resistor is: $33k\Omega \le R_{ILIM} \le 1.1M\Omega$ .
3	nFAULT	О	Active-Low Open-Drain Fault Output Flag Pin. nFAULT is asserted during over-current, over-voltage or over-temperature faults. Connect this pin with a pull-up resistor to a logic high voltage.
4	EN	I	Enable Logic Input. Pull the EN high to enable the power switch and drive it low to turn it off. Do not leave this pin float. EN voltage must be limited to remain in its recommended maximum rating if it is tied to $V_{IN}$ (< 6.5V).
5	GND	—	Ground Connection. Connect this pin to the exposed pad (EP) externally.
6	IN	I	Device Supply Voltage and Power Switch Input Pin. Decouple the IN pin to GND with a $0.1\mu$ F or larger ceramic capacitor, placed as close as possible to the device.
Exposed Pad	EP	—	Exposed Pad. EP is internally connected to the GND. Use EP as a heat sinking pad to the PCB ground plane and the GND pin.



# **ELECTRICAL CHARACTERISTICS**

 $(T_A = -40^{\circ}C \text{ to } +125^{\circ}C, 2.5V \le V_{IN} \le 6.5V, V_{EN} = V_{IN}, R_{ILIM} = 33k\Omega$ . Typical values are at  $T_A = +25^{\circ}C$ , unless otherwise noted. Current flow into a terminal is considered positive.)

PARAMETER	SYMBOL	CONDIT	IONS	MIN	TYP	MAX	UNITS
		$V_{IN} = 5V$ , No load on OUT	R <sub>ILIM</sub> = 33kΩ		190		
Quiescent Supply Current	ΙQ	$V_{\rm EN} = 5V$	$R_{ILIM} = 150 k\Omega$		190		μA
Chutdown Supply Current		V <sub>EN</sub> = 0V, V <sub>IN</sub> = 5V			0.9		цА
Shutdown Supply Current	I <sub>SD</sub>	$V_{EN}$ = 0V or 5V, $V_{IN}$ = 20V			150		μA
Reverse Leakage Current	I <sub>REV</sub>	$V_{OUT} = 6.5V, V_{IN} = V_{EN} = 0V,$ $T_A = +25^{\circ}C$	measure I <sub>OUT</sub> ,		3		μA
EN Terminal Input Threshold	V <sub>IH</sub>	V <sub>EN</sub> rising				1.1	- v
	V <sub>IL</sub>	V <sub>EN</sub> falling		0.4			
EN Terminal Leakage Current	I <sub>EN</sub>	$V_{EN}$ = 0V or 5.5V	V <sub>EN</sub> = 0V or 5.5V		0.1		μA
			T <sub>A</sub> = +25°C		55		
Switch Resistance <sup>(1)</sup>	R <sub>DS(ON)</sub>	$2.5V \le V_{IN} \le 5V$ , $I_{OUT} = 250mA$	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		55		mΩ
			$T_A = -40^{\circ}C$ to $+125^{\circ}C$		55		
OUT Discharge Resistance	R <sub>DIS</sub>	$V_{OUT} = 5V, V_{EN} = 0V$	ν, V <sub>EN</sub> = 0V		530		Ω
		R <sub>ILIM</sub> = 33kΩ			3010		- mA
Current Limit Threshold		R <sub>ILIM</sub> = 40.2kΩ			2500		
		R <sub>ILIM</sub> = 56kΩ	Can Figure 4		1810		
	l <sub>os</sub>	R <sub>ILIM</sub> = 80.6kΩ	See Figure 4		1270		
		R <sub>ILIM</sub> = 150kΩ			710		
		R <sub>ILIM</sub> = 1100kΩ			170		
Over-Voltage Lockout (IN Pin)							
OVLO Threshold Voltage	V <sub>OVLO</sub>	IN rising			7.6		V
Hysteresis (2)					190		mV
Voltage Clamp (OUT Pin)							
OUT Clamp Voltage Threshold	V <sub>ovc</sub>	$C_L = 1\mu F, R_L = 100\Omega, V_{IN} = 0$	6.5V		5.45		V
Under-Voltage Lockout (IN Pin)		•					
UVLO Threshold Voltage	V <sub>UVLO</sub>	V <sub>IN</sub> rising			2.32		V
UVLO Hysteresis (2)					30		mV
Thermal Shutdown					•	•	
Thermal Shutdown Threshold, OTSD2		T <sub>J</sub> increasing			155		°C
Thermal Shutdown Threshold OTSD1 (only in Current-Limit)					135		°C
Hysteresis (2)					20		°C
nFAULT Flag							_
nFAULT Output Resistance	R <sub>nFAULT</sub>	nFAULT is low and $I_{SINK} = 1$	mA		50		Ω
nFAULT Leakage Current	Infault	nFAULT is high			0.1		μA

#### NOTES:

1. The junction temperature is kept near the ambient temperature using pulse-test techniques for measuring these parameters, so, the thermal effects should be considered separately depending on the application.

2. Provided for reference only. Not guaranteed.



# TIMING REQUIREMENTS

 $(T_A = -40^{\circ}C \text{ to } +125^{\circ}C, 2.5V \le V_{IN} \le 6.5V, V_{EN} = V_{IN}, R_{ILIM} = 33k\Omega$ . Typical values are at  $T_A = +25^{\circ}C$ , unless otherwise noted. Current flow into a terminal is considered positive.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Power Switch						
V <sub>OUT</sub> Rise Time	t <sub>r</sub>	$V_{IN}$ =5V, C <sub>L</sub> = 1µF, R <sub>L</sub> = 100Ω, see Figure 2		2.8		ms
V <sub>out</sub> Fall Time	t <sub>f</sub>	$v_{\rm IN} = 5v, C_{\rm L} = 1\mu r, R_{\rm L} = 100\Omega, see Figure 2$		0.18		ms
Enable Input EN						
V <sub>OUT</sub> Turn-On Time	t <sub>on</sub>			8.4		ms
V <sub>OUT</sub> Turn-Off Time	t <sub>OFF</sub>	$V_{IN}$ =5V, $C_L$ = 1µF, $R_L$ = 100 $\Omega$ , see Figure 3		0.22		ms
Current Limit						
V <sub>OUT</sub> Short Circuit Response Time <sup>(3)</sup>	t <sub>ios</sub>	V <sub>IN</sub> = 5V, see Figure 4		3.5		μs
Over-Voltage Lockout (IN Pin)						•
$V_{IN}$ OVLO Turn-Off Delay $^{(3)}$	$t_{\rm OVLO\_off\_delay}$	$V_{\text{IN}}$ ramp up from 5V to 10V with 1V/µs rate, with 100 $\Omega$ load on $V_{\text{OUT}}$		0.6		μs
nFAULT Flag						
nFAULT Deglitch Time		nFAULT asserted due to an over-current event or de-asserted after clearing this event		8		ms

NOTE: 3. These parameters are provided for reference only.

# PARAMETER MEASUREMENT INFORMATION

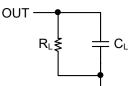


Figure 1. Test Load for  $V_{\text{OUT}}$  Rise and Fall



Figure 2. VOUT Power-On and Off Timing

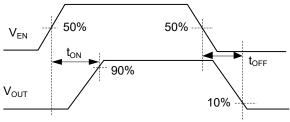


Figure 3. Enable Timing for VOUT

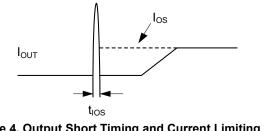
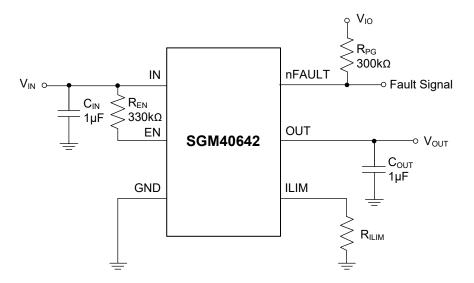


Figure 4. Output Short Timing and Current Limiting (I<sub>os</sub>) Parameters

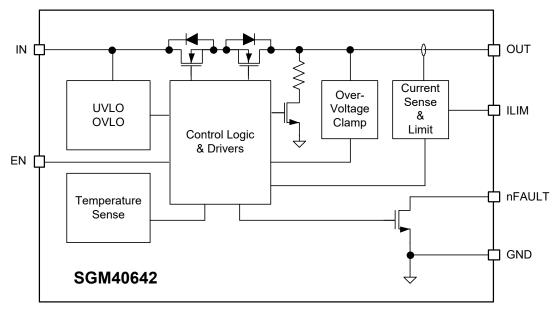


# **TYPICAL APPLICATION CIRCUIT**



NOTE: To select the R<sub>ILIM</sub> value, use either the Electrical Characteristics table (I<sub>OS</sub> row) or the I<sub>OS</sub> given by Equation 1. Figure 5. Typical Application Circuit

# FUNCTIONAL BLOCK DIAGRAM







# **DETAILED DESCRIPTION**

### Overview

The SGM40642 is a smart low voltage load switch with reliable over-current and over-voltage protections. It can be used as an eFuse for a wide range of applications including slave USB devices.

N-channel MOSFETs are used to build a current limited power switch in the device that can carry up to 2.5A load current continuously. The current limit is adjustable with an external resistor between 170mA and 2.9A. If the load tends to exceed the current limit, the switch enters constant-current mode. Having a precision over-current limit allows for lower input supply over design margins. This device also features a fast short circuit protection that disconnects the load from the supply when a short is detected on the load side.

The input tolerates over-voltage levels as high as 20V. The output ( $V_{OUT}$ ) is clamped to a precisely regulated 5.45V (TYP) voltage if the over-voltage is small ( $V_{IN}$  < 7.6V). The  $V_{OUT}$  will shut down if  $V_{IN}$  exceeds 7.6V.

Other features are summarized below:

• An active high enable input that can be used to put the load in sleep mode (especially useful for portable applications).

• Over-temperature safety protection that shuts down the device if a persistent over-current or small over-voltage (V<sub>OUT</sub> clamp) event lasts for a relatively long time and causes high die temperature.

• An active low deglitched fault reporting output (nFAULT) is also provided, that filters the nFAULT signal from rapid state changes to avoid false fault alerts.

• Output discharge capability (pull-down). This feature helps for making sure that the load is turned off output disable and is not in an undefined operational state.

• Reverse blocking feature (when the device is disabled) prevents any reverse power flow when an active load is controlled by the switch to avoid unwanted behavior.

### **Enable Input**

The enable is a TTL and CMOS compatible logic input that controls the device internal circuits and the power switch. A logic high enables the driver, control circuits, and power switch and a logic low will turn off the switch and reduces the supply current to very low levels.

This logic input has an internal protective Zener diode and can be pulled up to  $V_{IN}$  with a sufficiently large pull-up resistor (300k $\Omega$ ) to make sure the EN voltage does not exceed the absolute maximum rating when the IN is in over-voltage condition.

### **Internal Temperature Sensing**

The SGM40642 uses two independent temperature monitoring units to protect the switch and the device against overheating. The loss is mainly due to the current passing through the switch and the voltage drop across it. This switch voltage drop is high when the device is clamping the input voltage to keep the output at 5.45V. Also, when the switch operates in the constant-current mode during an over-current event, the voltage drop across the power switch is increased. The package power dissipation is proportional to the voltage drop across the switch. This loss will increase the junction temperature during an over-current event. The first temperature sensor (OTSD1) detects if the die temperature exceeds 135°C (TYP) and the device is in current limit mode. If this condition is detected, the switch will turn off. There is an almost 20°C hysteresis in the OTSD1 detection, and the switch turns on again after the device has cooled for almost 20°C.

The SGM40642 has a second die temperature sensor (OTSD2) as well. If the die temperature exceeds 155 $^{\circ}$ C (TYP), the switch is turned off by OTSD2, regardless of the switch current level. The OSTD2 protection also has a hysteresis of 20 $^{\circ}$ C and the switch recovers it's on state automatically if the junction cools down by approximately 20 $^{\circ}$ C below the turn-off threshold.

Both types of thermal protections can cause cyclic ON and OFF periods for the switch until the fault condition is cleared.



# **DETAILED DESCRIPTION (continued)**

### **Overload Protection**

In case of an overload, the output current is limited to the  $I_{OS}$  level as shown in Figure 4. The output voltage is reduced to maintain the constant output current at the limited level.

If a persistent overload condition occurs, the current will be limited to the programmed  $I_{OS}$ . This event can lead to an OTSD1 switch shutdown at 135°C that initiates the thermal protection cycling to protect the device against the overload.

An overload or output short event may occur in two possible situations.

In the first case a short or partial short occurs when the device is powering-up or is being enabled. In this case the output voltage will be held near zero and the current ramps to the  $I_{OS}$  level. The current remains at the  $I_{OS}$  level until the fault condition is cleared or thermal protection cycling begins (due to the OTSD1).

In the second case the short, partial short, or a transient overload occurs when the device is already powered. If this happens, the device will react to the over-current, but the current peak can momentarily go above  $I_{OS}$  for a short  $t_{IOS}$  time (Figure 4). The high current peak overdrives the current sense circuit that leads to a brief switch disable period. After a short time, the current sense circuit recovers, and the output current will be limited to  $I_{OS}$ . The current limiting to  $I_{OS}$  is continued until the fault is cleared or a thermal cycling begins.

### nFAULT Output Flag

The nFAULT is an active-low open-drain output that should be pulled up to a low voltage logic rail. It will be asserted when a fault occurs (over-current, over-temperature or over-voltage) and remains low until the fault is cleared and the device enters normal operation. The nFAULT is not asserted when the device operates in output clamp mode.

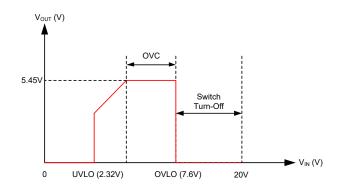
False over-current reporting is avoided by considering an 8ms (TYP) internal deglitch delay only for over-current to assure that nFAULT is not mistakenly asserted due to a non-fault situation such as powering a large capacitive load. The deglitch delay applies for both entering in and existing out of an over-current fault event. Particularly, the nFAULT is not deglitched due to an over-temperature fault caused by over-current, but it is deglitched after the device has cooled and the switch is turned on. By such asymmetric deglitch strategy nFAULT oscillation during an over-temperature event is avoided. The nFAULT is not deglitched when the switch is disabled due to an OVLO or recovery from OVLO.

### **Output Discharging**

When the device is disabled or is in UVLO or OVLO condition, the output is discharged with an internal 530 $\Omega$  (TYP) resistive path to remove any remaining charge or leakage current on the output. The path resistance increases at lower V<sub>IN</sub> values.

### **Functional Modes**

The SGM40642 can tolerate up to 20V input voltage. The 0V to 20V input range can be split into four segments in such a way that in each segment the device operates in a different mode as shown in Figure 7.







# **DETAILED DESCRIPTION (continued)**

#### Mode 1: Input Under-Voltage Lockout (UVLO)

If the input voltage is below the 2.32V (TYP) under-voltage lockout level (UVLO), the power switch will be disabled. The switch cannot turn on until the input voltage exceeds the UVLO turn-on threshold. A 30mV hysteresis is considered for the UVLO comparator to avoid unwanted cycling for minor input voltage droops such as the droops caused by load connection during switch turn-on.

#### Mode 2: Over-Current Protection (OCP)

When  $V_{IN}$  is in the 2.32V to 5.45V range, the switch acts as a conventional power switch with a small series resistance with over-current protection.

#### Mode 3: Over-Voltage Clamp (OVC)

In the 5.45V to 7.6V input range, the output voltage is clamped to 5.45V. The over-current protection is active in the OVC mode.

#### Mode 4: Over-Voltage Lockout (OVLO)

If V<sub>IN</sub> exceeds 7.6V, the switch will be turned off to isolate the load from the input (OVLO mode).



# **APPLICATION INFORMATION**

The SGM40642 is a smart 5V load switch (also known as eFuse) with over-voltage clamping and accurate current limiting capabilities. As shown in Figure 8, when a peripheral USB device (slave) is hot plugged or unplugged, the voltage transient caused by the rapid current change in the parasitic inductance of the cable can damage the slave device. Using the SGM40642 at the USB port of the slave device can protect it against such transients. Such transients may also occur when the cable is already connected and the SGM40642 is turned off in response to a fault. Using the SGM40642, there is no need for bulk bypass capacitors, TVS diodes or other external over-voltage protection components in the input port of the slave device. As a controlled switch, the SGM40642 can also be used in a USB master device (host). It is pin-to-pin compatible with the SGM2553.

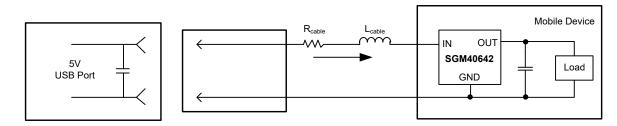


Figure 8. SGM40642 Used to Protect a 5V USB Salve Device (Mobile) against Hot Plug or Turn-Off Transients Caused by the Cable Parasitic Impedance

### **Design Requirements**

The design parameters for this example are listed in Table 1.

#### Table 1. Design Parameters (Example)

DESIGN PARAMETERS	VALUE
Normal Input Operation Voltage	5V
Output Transient Voltage	6.5V
Minimum Current Limit	TBD
Maximum Current Limit	TBD

### **Detailed Design Procedure**

As the first step, the main parameters of the design must be chosen or determined carefully similar to the Table 1.

#### Input and Output Capacitance

Adding capacitors to the device input and output ports are important to improve the device performance. For most applications, a 0.1µF or larger decoupling capacitor between the IN and GND pins is sufficient. The optimal value may vary depending on the application.

When  $V_{IN}$  ramps up,  $V_{OUT}$  follows  $V_{IN}$  until 5.4V and then it will be clamped at this level (OVC) until  $V_{IN}$  reaches the 7.6V (OVLO level). If  $V_{IN}$  rises above OVLO level, the switch will turn off after the  $t_{OVLO_off_delay}$  delay. This delay is highly dependent on the  $V_{IN}$  rising rate, and  $V_{OUT}$  will confront some peak voltages for a short time before falling. Using an output capacitance helps reducing such output peak as shown in Figure 9.



## **APPLICATION INFORMATION (continued)**

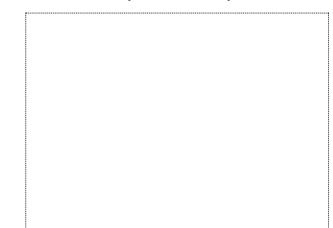


Figure 9. VOUT Overshoot Peak Voltage vs. COUT when VIN Steps from 5V to 15V with 1V/µs Rising Rate

#### **Current Limit Programming**

An external resistor ( $R_{ILIM}$ ) placed between the ILIM pin and GND sets the switch over-current threshold limit ( $I_{OS}$ ). The ILIM pin voltage is regulated by an internal control loop. The current limit threshold is proportional to the current pulled from the ILIM pin by the resistor. An  $R_{ILIM}$  resistor in the 33k $\Omega$  to 1.1M $\Omega$  range is recommended for stable internal loop operation. Use short trace routes for the  $R_{ILIM}$  on the PCB to minimize the impact of parasitics and noise on the accuracy of the current limit setting.

In many applications the tolerance of the current limit threshold is important, so the minimum current limit level and the maximum current limit level are specified as design parameters. The  $R_{ILIM}$  value should be selected carefully such that in the worst tolerance cases, the current limit is guaranteed to fall between those two limits. Setting the current limit above a minimum is important to assure a smooth start up with no hiccup at full load or for highly capacitive loads. Similarly, setting the current limit below a maximum is important to avoid input voltage droops due to source overloading or source current limit activation.

Equation 1 gives typical over-current threshold (I<sub>OS</sub>) and its tolerance (min and max) for a given R<sub>ILIM</sub> resistor:

$$I_{OS(max)}(mA) = \frac{96754V}{R_{ILIM}^{0.985}k\Omega} + 30$$

$$I_{OS(typ)}(mA) = \frac{98322V}{R_{ILIM}^{1.003}k\Omega}$$

$$I_{OS(min)}(mA) = \frac{97399V}{R_{ILIM}^{1.015}k\Omega} - 30$$
(1)

The R<sub>ILIM</sub> values for some specific current limit thresholds are provided in the Electrical Characteristics table.

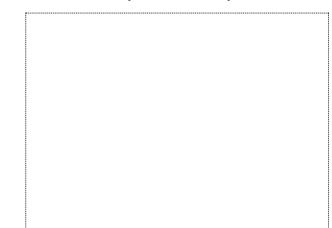
R<sub>ILIM</sub> can be selected to set a current limit threshold above a minimum load, or below a maximum load current.

Current limit resistor can also be designed using the  $I_{OS}$ -R<sub>ILIM</sub> graphs in Figure 10 and Figure 11 for higher (> 500mA) and lower (< 700mA) current levels respectively.

To assure that the current limit is above a minimum threshold, on the  $I_{OS(min)}$  curve, find the  $R_{ILIM}$  value at the maximum desired load current and choose the  $R_{ILIM}$  resistor below that. The actual maximum current-limit threshold will be the value on the  $I_{OS(max)}$  curve at the selected  $R_{ILIM}$  value.



## **APPLICATION INFORMATION (continued)**



# Figure 10. SGM40642 Current Limit Threshold (I<sub>os</sub>) vs. Current Limit Programming Resistor (R<sub>ILIM</sub>) for Higher Current Range ( $33k\Omega < R_{ILIM} < 150k\Omega$ )

To assure that the maximum current limit is below a threshold, on the  $I_{OS(max)}$  curve find the  $R_{ILIM}$  value at the desired maximum load current and choose the  $R_{ILIM}$  resistor above this value. The actual minimum current-limit threshold will be the value on the  $I_{OS(min)}$  curve at the selected  $R_{ILIM}$  value.



Figure 11. SGM40642 Current Limit Threshold (I<sub>os</sub>) vs. Current Limit Programming Resistor (R<sub>ILIM</sub>) for Lower Current Range ( $150k\Omega < R_{ILIM} < 1100k\Omega$ )

### Programming Current Limit above a Minimum

In some applications it is necessary to make sure that the current is not limited below a certain minimum. For example, if the load needs 2.1A current, the minimum current limit threshold must be above 2100mA, considering all circuit variations and tolerances. Using  $I_{OS(min)}$  = 2100mA in Equation 1 to find  $R_{ILIM}$ :

$$R_{ILIM}(k\Omega) = \left(\frac{97399}{I_{OS(min)} + 30}\right)^{\frac{1}{1.015}} = 43.22k\Omega$$
(2)

The nearest 1% resistor below the calculated value is:

$$R_{ILIM} = 42.2k\Omega$$
.

With this resistor, the minimum current limit is:

$$I_{OS(min)}(mA) = \frac{97399V}{R_{ILIM}^{1.015}k\Omega} - 30 = 2130mA$$
(3)



# **APPLICATION INFORMATION (continued)**

Note that  $R_{ILIM} = 1.01 \times 42.2 k\Omega = 42.62 \Omega$  is used in (3) to include resistor tolerance for calculating the lowest possible  $I_{OS(min)}$ .

Similarly, the maximum possible current limit threshold considering the 1% tolerance of the resistor ( $R_{ILIM} = 0.99 \times 42.2 k\Omega = 41.78\Omega$ ) is:

$$I_{OS(max)}(mA) = \frac{96754V}{R_{ILIM}^{0.985}k\Omega} + 30 = 2479mA$$
(4)

So, with  $R_{ILIM} = 42.2k\Omega \pm 1\%$  the switch current limit threshold is assured to be above 2130mA and below 2479mA.

#### Programming Current Limit below a Maximum

Other applications may need an assured maximum level for the current limiting. For example, suppose that a load requires 2.9A, so the minimum current limit threshold is 2900mA. Using Equation (1) with  $I_{OS(max)}$  = 2900mA, results in  $R_{ILIM}$  = 35.57k $\Omega$  and the closest larger 1% resistor is  $R_{ILIM}$  = 36k $\Omega$ . With this resistor and inserting the worst case value ( $R_{ILIM}$  = 0.99 × 36k $\Omega$ ), the actual maximum limit is calculated as  $I_{OS(max)}$  = 2894mA and the minimum actual limit (by inserting  $R_{ILIM}$  = 1.01 × 36k $\Omega$ ) is  $I_{OS(min)}$  = 2508mA. So, with  $R_{ILIM}$  = 36k $\Omega$  ± 1%, the current limit threshold is assured to be higher than 2508mA and below 2894mA (≈ 2.9A).

#### Loss Analysis and Die Temperature

Estimating the power loss and junction temperature rise is a good design practice to make sure the system using the device will have a reliable performance. In this section, a simplified thermal analysis method is provided for the SGM40642. Note that other operating or environmental factors of the system such as ventilation, PCB copper thickness and connected area and the nearby components losses have a strong impact on the thermal performance and must be considered in every specific application. The loss analysis is done in both component level and system level to assure a good design.

The small on-resistance ( $R_{ON}$ ) of the internal switch allows to have high current and high power-density is a small package. For thermal analysis  $R_{ON}$  variations against  $V_{IN}$  and  $T_A$  (ambient temperature) should be considered. For initial estimate, consider the highest expected operating ambient temperature ( $T_e$ ) and evaluate the  $R_{ON}$  from the typical characteristics graph. For the SGM40642 if  $V_{IN} < V_{OVC}$ , the maximum loss can be estimated by:

$$P_{\rm D} = R_{\rm ON} \times I_{\rm OUT}^{2}$$
(5)

If  $V_{OVC} < V_{IN} < V_{OVLO}$  the output clamps to the  $V_{OVC}$  and the loss is given by:

$$P_{D} = (V_{IN} - V_{OVC}) \times I_{OUT}$$
(6)

where

- P<sub>D</sub> = Maximum device power loss (W)
- $R_{ON}$  = Switch on-resistance ( $\Omega$ )
- V<sub>OVC</sub> = Over-voltage clamp voltage (V)
- I<sub>OUT</sub> = Maximum current limit threshold (A)

The junction temperature can be calculated from:

$$T_{J} = P_{D} \times \theta_{JA} + T_{A} \tag{7}$$

#### where

- T<sub>A</sub> = Ambient temperature (°C)
- $\theta_{JA}$  = Device thermal resistance (°C/W)

• T<sub>J</sub> = Junction temperature (°C)

Based on the highest current limit setting and the device thermal resistance on the PCB calculate  $T_J$  and compare it with the initial temperature considered for evaluating  $R_{ON}$  ( $T_e$ ). If the difference is negligible, the estimate is no problem, otherwise repeat the calculation by considering the new  $R_{ON}$  value based on the calculated  $T_J$ . Usually after two or three iterations the desired result is achieved. If there is no convergence, make a more reasonable  $T_e$  assumption. Note that the thermal resistance  $\theta_{JA}$  is highly dependent on the PCB and its value is critical in determination of the junction temperature.



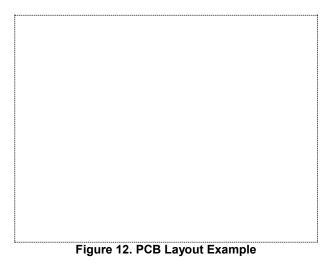
# **APPLICATION INFORMATION (continued)**

### Source Supply Voltage Range

The SGM40642 is designed to operate with 2.7V to 5V rails. The  $V_{OUT}$  clamping at 5.45V is a protection feature and is not intended to be used as a regulator.

### Layout Considerations

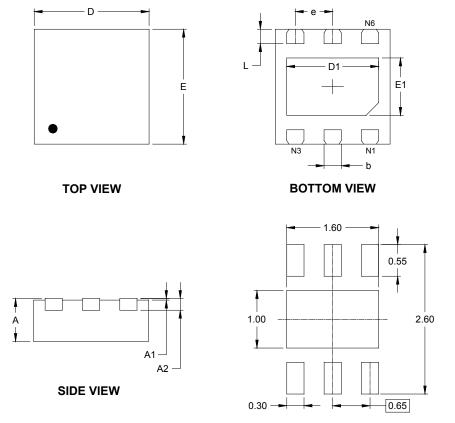
- Use a  $0.1\mu F$  or larger ceramic capacitor to bypass  $V_{IN}$  to GND and place it as close as possible to the device.
- Use a low ESR ceramic capacitor on output selected based on Figure 9 and design guidelines.
- ${\boldsymbol{\cdot}}$  Use short traces to connect the  $R_{\text{ILIM}}$  resistor and the device.
- Connect the device EP pad directly on the PCB ground or through a wide and short copper trace.





# PACKAGE OUTLINE DIMENSIONS

# TDFN-2×2-6AL



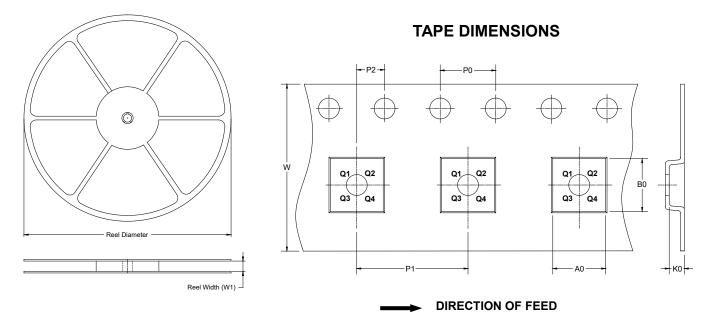
RECOMMENDED LAND PATTERN (Unit: mm)

Symbol	-	nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	3 REF	0.008 REF		
D	1.900	2.100	0.075	0.083	
D1	1.500	1.700	0.059	0.067	
E	1.900	2.100	0.075	0.083	
E1	0.900	1.100	0.035	0.043	
b	0.250	0.350	0.010	0.014	
е	0.650	BSC	0.026	BSC	
L	0.174	0.326	0.007	0.013	



# TAPE AND REEL INFORMATION

### **REEL DIMENSIONS**

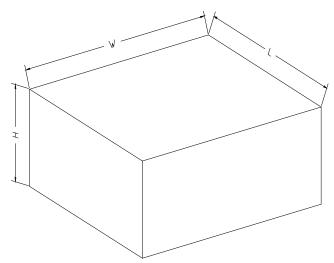


NOTE: The picture is only for reference. Please make the object as the standard.

## KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TDFN-2×2-6AL	7″	9.5	2.30	2.30	1.10	4.0	4.0	2.0	8.0	Q1

## **CARTON BOX DIMENSIONS**



NOTE: The picture is only for reference. Please make the object as the standard.

## **KEY PARAMETER LIST OF CARTON BOX**

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton	
7" (Option)	368	227	224	8	
7"	442	410	224	18	DD0002

